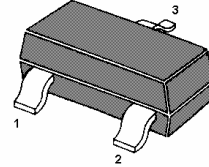


NPN General Purpose Amplifier

For low noise, high gain, general purpose amplifier applications at collector currents from 1 μ A to 50mA.



1. Base 2. Emitter 3. Collector

Marking: 1RM

SOT-23 Plastic Package

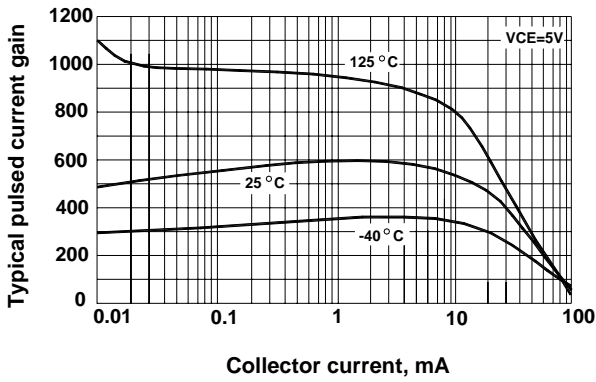
Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

	Symbol	Value	Unit
Collector Emitter Voltage	V_{CEO}	25	V
Collector Base Voltage	V_{CBO}	30	V
Emitter Base Voltage	V_{EBO}	4.5	V
Collector Current - Continuous	I_C	100	mA
Total Device Dissipation Derate above 25 $^\circ\text{C}$	P_{tot}	200 2.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Operating and Storage Junction Temperature Range	T_J, T_S	-55 to +150	$^\circ\text{C}$

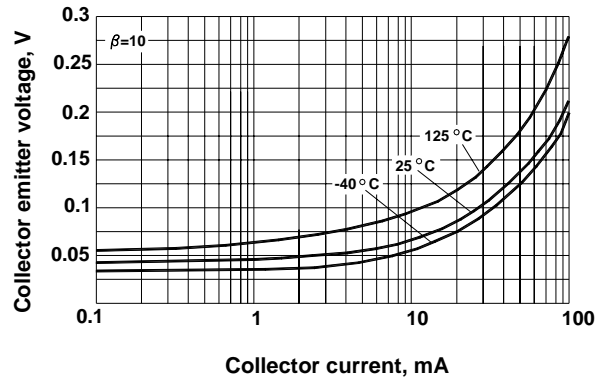
Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Max.	Unit
DC Current Gain				
at $V_{CE}=5\text{V}$, $I_C=100\mu\text{A}$	h_{FE}	400	1200	-
at $V_{CE}=5\text{V}$, $I_C=1\text{mA}$	h_{FE}	450	-	-
at $V_{CE}=5\text{V}$, $I_C=10\text{mA}$	h_{FE}	400	-	-
Small Signal Current Gain				
at $V_{CE}=5\text{V}$, $I_C=1\text{mA}$, $f=1\text{KHz}$	h_{fe}	450	1800	-
Collector Base Breakdown Voltage				
at $I_C=100\mu\text{A}$	$V_{(BR)CBO}$	30	-	V
Collector Emitter Breakdown Voltage				
at $I_C=1\text{mA}$	$V_{(BR)CEO}$	25	-	V
Collector Emitter Saturation Voltage				
at $I_C=10\text{mA}$, $I_B=1\text{mA}$	V_{CEsat}	-	0.5	V
Base Emitter On Voltage				
at $I_C=10\text{mA}$, $V_{CE}=5\text{V}$	V_{BEon}	-	0.8	V
Collector Cutoff Current				
at $V_{CB}=15\text{V}$	I_{CBO}	-	50	nA
Emitter Cutoff Current				
at $V_{EB}=3\text{V}$	I_{EBO}	-	50	nA
at $V_{EB}=4.5\text{V}$	I_{EBO}	-	100	nA
Gain Bandwidth Product				
at $V_{CE}=5\text{V}$, $I_C=500\mu\text{A}$, $f=20\text{MHz}$	f_T	50	-	MHz
Collector Base Capacitance				
at $V_{CB}=5\text{V}$, $f=100\text{KHz}$	C_{cb}	-	4	pF
Emitter Base Capacitance				
at $V_{BE}=0.5\text{V}$, $f=100\text{KHz}$	C_{eb}	-	10	pF
Noise Figure				
at $V_{CE}=5\text{V}$, $I_C=100\mu\text{A}$, $R_s=10\text{K}\Omega$, $f=10\text{Hz}$ to 15.7KHz	NF	-	2	dB

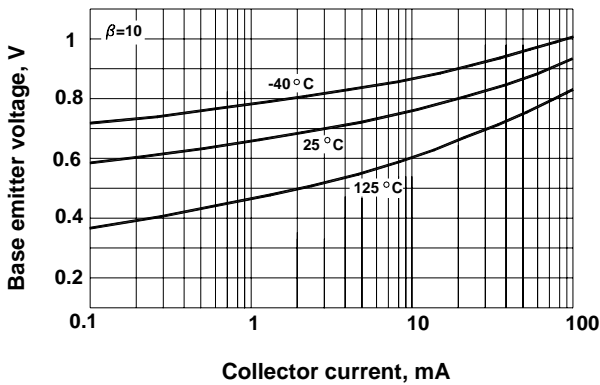
Typical pulsed current gain vs. collector current



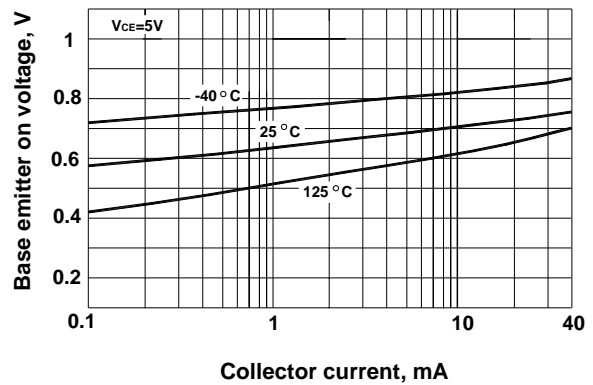
Collector emitter saturation voltage vs. collector current



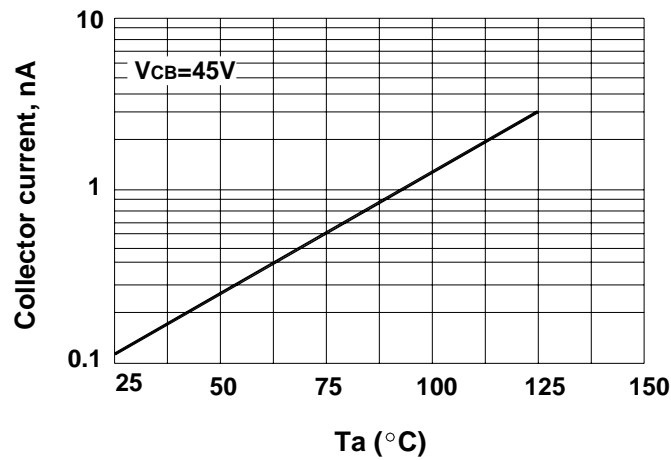
Base emitter saturation voltage vs. collector current



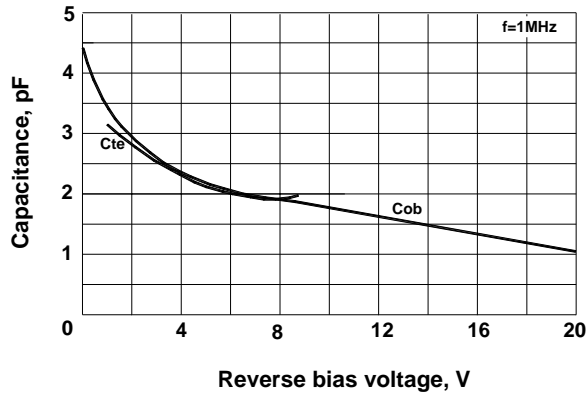
Base emitter on voltage vs. collector current



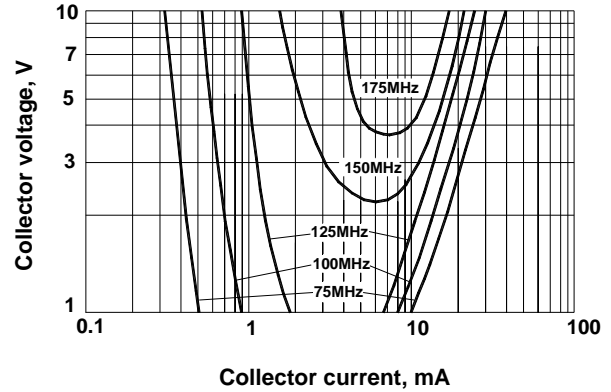
Collector cutoff current vs. ambient temperature



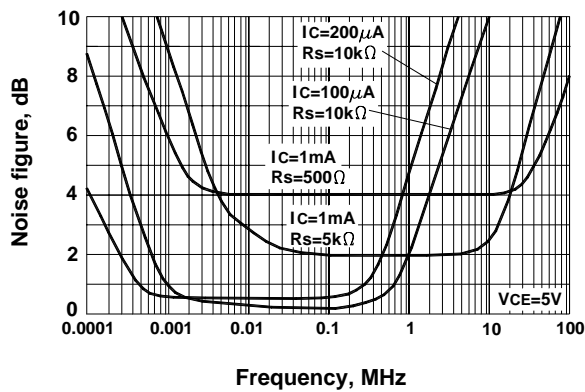
Input and output capacitance vs. reverse bias voltage



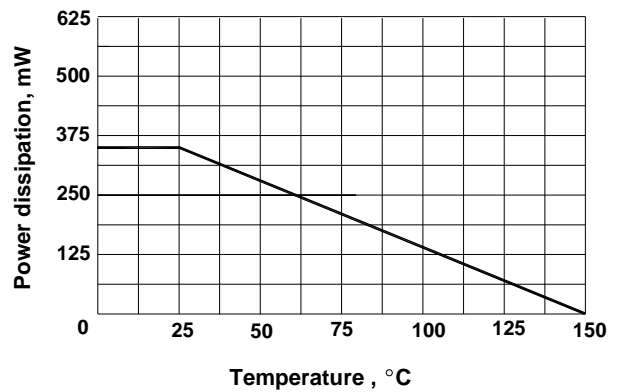
Contours of constant gain bandwidth product



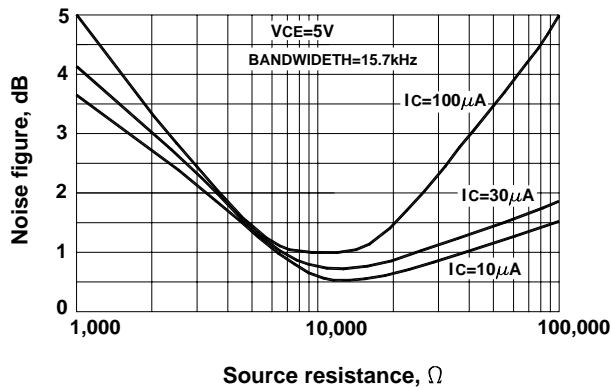
Noise figure vs. frequency



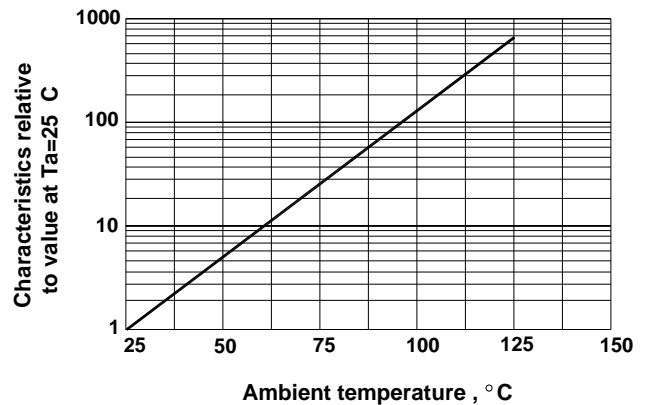
Power dissipation vs. ambient temperature



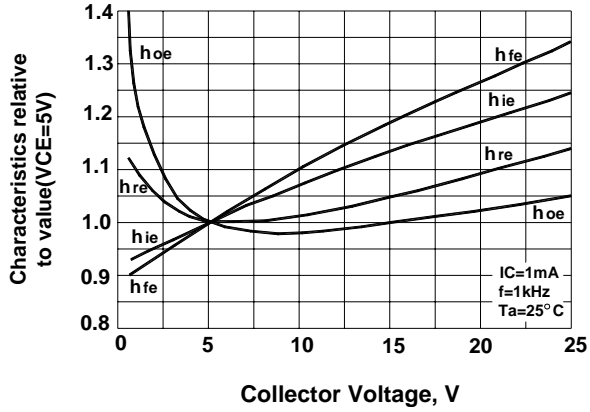
Wideband noise frequency vs. source resistance



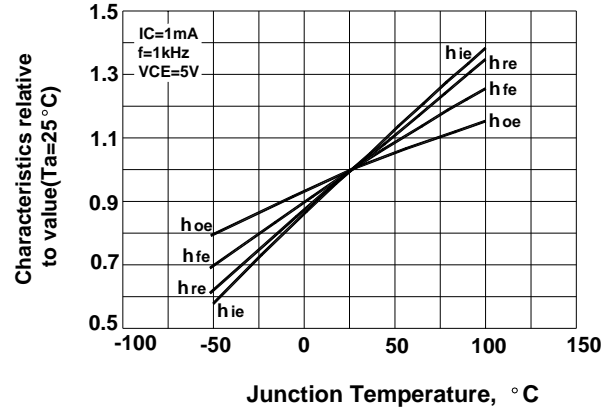
Normalized collector cutoff current vs. ambient temperature



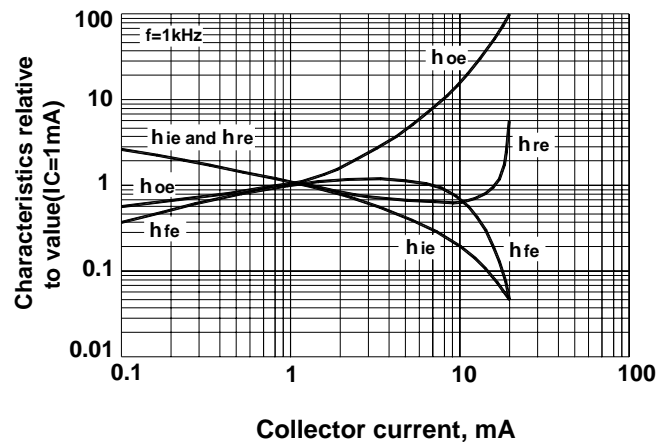
Typical common emitter characteristics



Typical common emitter characteristics



Typical common emitter characteristics



单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES\(时科\)](#)